# **Single Inverter**

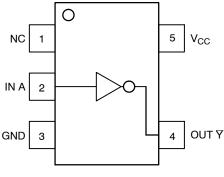
The MC74VHC1G04 is an advanced high speed CMOS inverter fabricated with silicon gate CMOS technology.

The internal circuit is composed of multiple stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1G04 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1G04 to be used to interface 5 V circuits to 3 V circuits.

#### Features

- High Speed:  $t_{PD} = 3.5 \text{ ns} (Typ) \text{ at } V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 105
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant



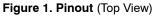


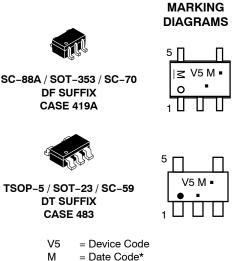


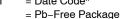
Figure 2. Logic Symbol



# **ON Semiconductor®**

http://onsemi.com





(Note: Microdot may be in either location)

\*Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT				
1	NC			
2	IN A			
3	GND			
4	OUT Y			
5	V <sub>CC</sub>			

#### FUNCTION TABLE

A Input	<b> Y</b> Output
L	Н
Н	L

## **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### MAXIMUM RATINGS

Symbol		Value	Unit	
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC}$ $+0.5$	V
Ι <sub>ΙΚ</sub>	DC Input Diode Current		-20	mA
Ι <sub>ΟΚ</sub>	DC Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Sink Current		±12.5	mA
I <sub>CC</sub>	DC Supply Current per Supply Pin		±25	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case	for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias		+ 150	°C
$\theta_{JA}$	Thermal Resistance	SC70-5/SC-88A (Note 1) TSOP-5	350 230	°C/W
PD	Power Dissipation in Still Air at 85°C	SC70–5/SC–88A TSOP–5	150 200	mW
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
I <sub>Latchup</sub>	Latchup Performance	Above V <sub>CC</sub> and Below GND at 125°C (Note 5)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

3. Tested to EIA/JESD22-A115-A.

4. Tested to JESD22-C101-A.

5. Tested to EIA/JESD78.

#### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0.0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $\begin{array}{ll} V_{CC}=3.3~V\pm0.3~V\\ V_{CC}=5.0~V\pm0.5~V \end{array}$	0 0	100 20	ns/V

#### DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

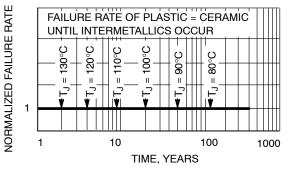


Figure 3. Failure Rate vs. Time Junction Temperature

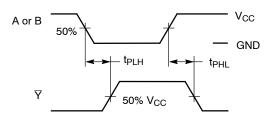
### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	٦	Γ <sub>A</sub> = 25°0	C	T <sub>A</sub> ≤	85°C	- 55°C 1	to 125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA} \end{cases}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		10		40	μΑ

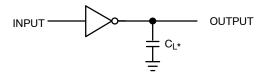
### AC ELECTRICAL CHARACTERISTICS Input $t_r = t_f = 3.0 \text{ ns}$

			٦	a = 25°0	2	<b>T</b> <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay,	$\begin{array}{l} V_{CC}=3.3\pm0.3\;V  C_L=15\;pF\\ C_L=50\;pF \end{array}$		4.5 6.4	7.1 10.6		8.5 12.0		10.0 14.5	ns
	Input A to Y	$\begin{array}{c} V_{CC} = 5.0 \pm 0.5 \; V \  \  C_L = 15 \; pF \\ C_L = 50 \; pF \end{array}$		3.5 4.5	5.5 7.5		6.5 8.5		8.0 10.0	
C <sub>IN</sub>	Maximum Input Capacitance			4	10		10		10	pF
						Турі	cal @ 25	5°C, V <sub>CC</sub> =	5.0 V	
C <sub>PD</sub>	Power Dissipation Ca	C <sub>PD</sub> Power Dissipation Capacitance (Note 6)						8.0		pF

6.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .







\*Includes all probe and jig capacitance. A 1–MHz square input wave is recommended for propagation delay tests.

#### Figure 5. Test Circuit

#### ORDERING INFORMATION

Device	Device Package			
MC74VHC1G04DFT1G				
NLVVHC1G04DFT1G*	SC70–5 / SC–88A / SOT–353			
MC74VHC1G04DFT2G	(Pb-Free)	3000/Tape & Reel		
NLVVHC1G04DFT2G*				
MC74VHC1G04DTT1G	SOT23–5 / TSSOP–5 / SC59–5 (Pb–Free)			

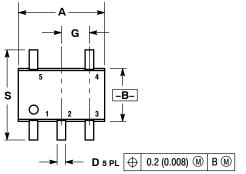
+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

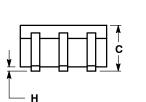
\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

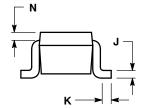
## **PACKAGE DIMENSIONS**

## SC-88A (SC-70-5/SOT-353) CASE 419A-02

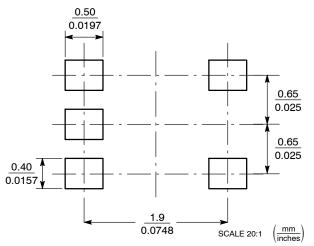
**ISSUE L** 







SOLDER FOOTPRINT



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI V14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. 419A-01 OBSOLETE. NEW STANDARD 419A-02. 4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.071	0.087	1.80	2.20
В	0.045	0.053	1.15	1.35
C	0.031	0.031 0.043		1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65 BSC	
Н		0.004		0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.004 0.012		0.30
N	0.008 REF		0.20	REF
S	0.079	0.087	2.00	2.20

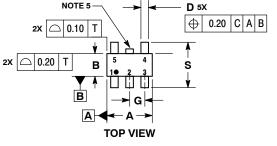
#### PACKAGE DIMENSIONS

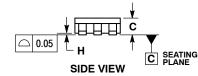


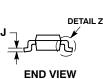
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- VIA.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL 3.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD
- FILASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A.
  OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY

	MILLIMETERS					
DIM	MIN MAX					
Α	3.00	BSC				
в	1.50	1.50 BSC				
С	0.90	1.10				
D	0.25	0.50				
G	0.95	BSC				
н	0.01	0.10				
J	0.10	0.26				
к	0.20	0.60				
М	0 °	10 °				
S	2.50 3.00					

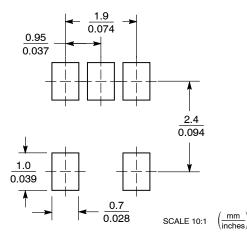






DETAIL Z

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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